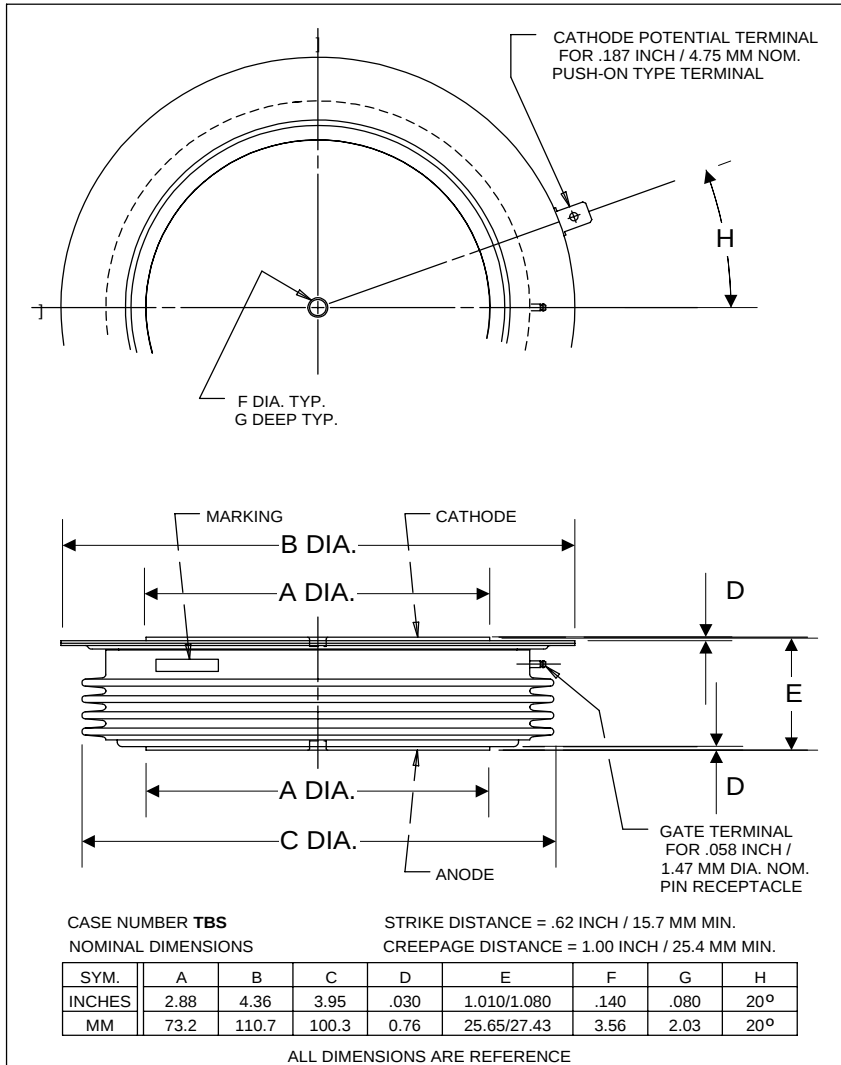
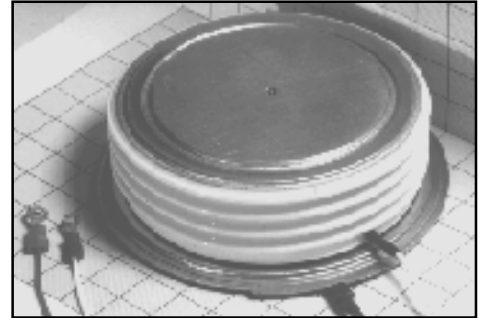




Description:

Powerex Silicon Controlled Rectifiers (SCR) are designed for phase control applications. These are all-diffused, hermetic Pow-R-Disc devices employing the field-proven amplifying gate.



Features:

- Low On-State Voltage
- High di/dt Capability
- High dv/dt Capability
- Excellent Surge and I²t Ratings

Applications:

- Power Supplies
- Motor Controllers

Ordering Information

Select the complete 12 digit device part number from the table below.

Type	Voltage V_{DRM} V_{RRM}	Current $I_{T(av)}$	Turn-Off t_q	Gate Current I_{GT}	Lead Code
TBS7	22 24 26	25	0	3	DH
	2200 V 2400 V 2600 V	2500 A	350 μ s typical	200 mA	12"

Absolute Maximum Ratings

Characteristics	Symbol		Units
Non-repetitive Transient Peak Reverse Voltage	V_{RSM}	$V_{RRM}+100V$	V
RMS On-State Current, $T_C=80^{\circ}C$	$I_{T(RMS)}$	3925	A
Average Current 180° Sine Wave, $T_C=80^{\circ}C$	$I_{T(AV)}$	2500	A
Peak One Cycle Surge On-State Current (Non-Repetitive) 60Hz	I_{TSM}	45,000	A
Peak One Cycle Surge On-State Current (Non-Repetitive) 50Hz	I_{TSM}	41,500	A
Critical Rate-of-Rise of On-State Current (Non-Repetitive)	di/dt	600	A/ μs
Critical Rate-of-Rise of On-State Current (Repetitive)	di/dt	100	A/ μs
I^2t for Fusing for One Cycle, 60 Hz	I^2t	8.43×10^6	A ² s
Peak Gate Power Dissipation	P_{GM}	250	W
Average Gate Power Dissipation	$P_{G(av)}$	35	W
Operating Temperature	T_J	-40 to 125°C	°C
Storage Temperature	T_{STG}	-40 to 150°C	°C
Mounting Force		6000 to 10000 26.6 to 44.4	lb. kN

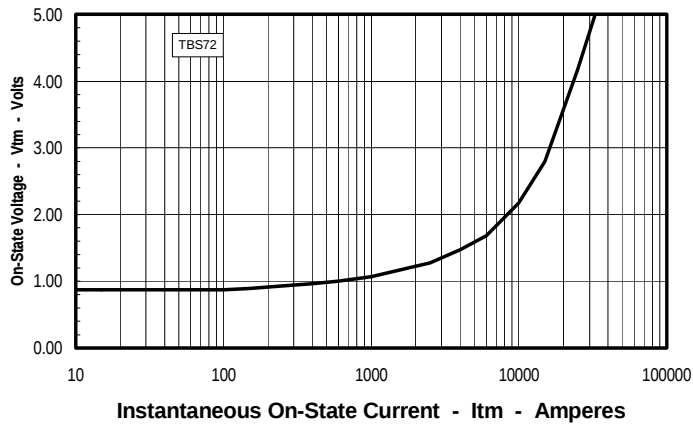
Electrical Characteristics, $T_J=25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Repetitive Peak Reverse Leakage Current	I_{RRM}	$T_J=125^\circ\text{C}$, $V_R=V_{RRM}$			150	mA
Repetitive Peak Forward Leakage Current	I_{DRM}	$T_J=125^\circ\text{C}$, $V_D=V_{DRM}$			150	mA
Peak On-State Voltage	V_{TM}	$T_J=125^\circ\text{C}$, $I_{TM}=2000\text{A}$ Duty Cycle < 0.01%			1.22	V
Threshold Voltage, Low-level	$V_{(TO)1}$	$T_J=125^\circ\text{C}$, for $375\text{A} \leq I_{TM} < 7800\text{A}$			0.9496	V
Slope Resistance, Low-level	r_{T1}				0.1234	m Ω
Threshold Voltage, High-level	$V_{(TO)2}$	$T_J=125^\circ\text{C}$, for $I_{TM} > 7800\text{A}$			1.10	V
Slope Resistance, High-level	r_{T2}				0.1149	m Ω
ABCD V_{TM} Modeling Coefficients	$A = 0.89085$	$T_J=125^\circ\text{C}$, for $10\text{A} \leq I_{TM} < 60,000\text{A}$				V
	$B = -2.419\text{E-}2$					-
	$C = 8.257\text{E-}5$	$A + B \times \ln(I_{tm}) + C \times I_{tm} +$				m Ω
	$D = 7.861\text{E-}3$	$D \times \text{Sqrt}(I_{tm})$				-
Typical Delay Time	t_d	$T_J = 125^\circ\text{C}$, $V_D=1500\text{V}$		3		μs
Maximum Turn-Off Time	t_q	$T_J=125^\circ\text{C}$, $I_T=2000\text{A}$, $di_R/dt=5\text{A}/\mu\text{s}$ $dv/dt=1000\text{V}/\mu\text{s}$ linear to 1000 V		250		μs
Minimum Critical dv/dt - Exponential to V_{DRM}	dv/dt	$T_J=125^\circ\text{C}$	500			V/ μs
Gate Trigger Current	I_{GT}	$T_J=25^\circ\text{C}$, $V_D=12\text{V}$			250	mA
Gate Trigger Voltage	V_{GT}	$T_J=25^\circ\text{C}$, $V_D=12\text{V}$			4.2	V
Non-Triggering Gate Voltage	V_{GDM}	$T_J=125^\circ\text{C}$, $V_D=V_{DRM}$			0.5	V
Peak Forward Gate Current	I_{GTM}				20	A
Peak Reverse Gate Voltage	V_{GRM}				20	V

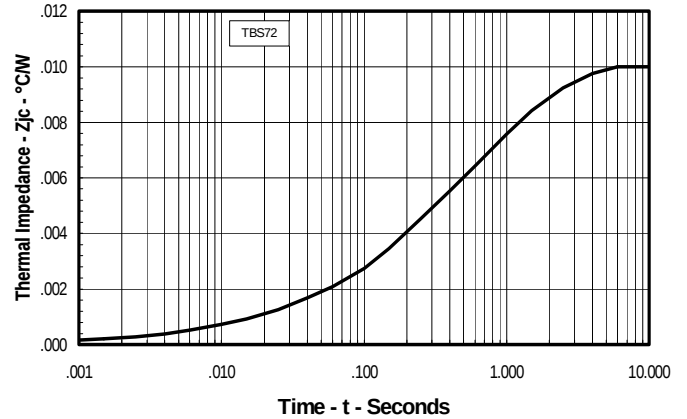
Thermal Characteristics

Characteristics	Symbol	Min.	Typ.	Max.	Units
Maximum Thermal Resistance, Double Sided Cooling					
Junction to Case	$R_{\theta JC}$			.010	$^\circ\text{C}/\text{W}$
Case to Sink	$R_{\theta CS}$			.002	$^\circ\text{C}/\text{W}$

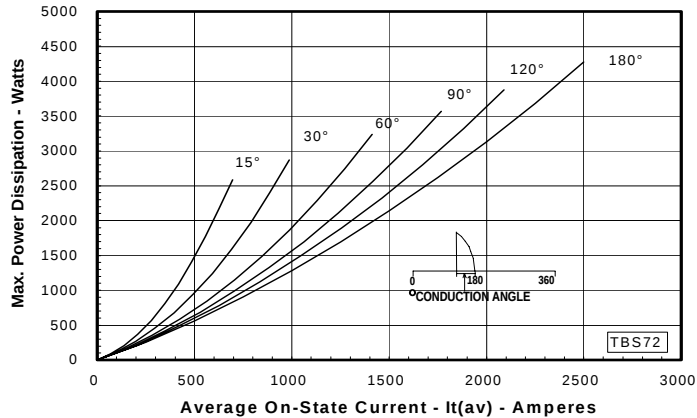
Maximum On-State Forward Voltage Drop
($T_j = 125^\circ\text{C}$)



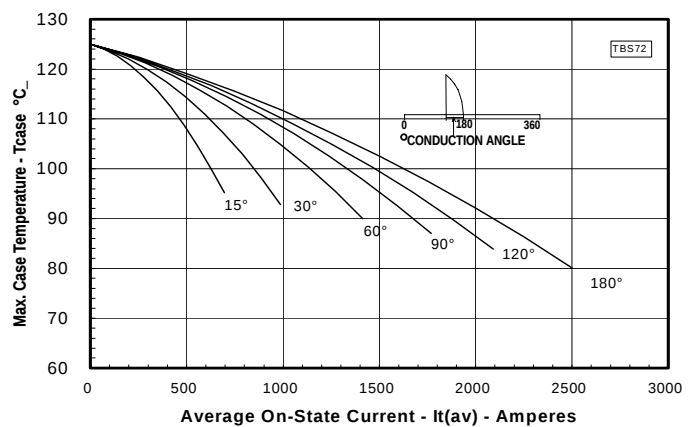
Maximum Transient Thermal Impedance
(Junction to Case)



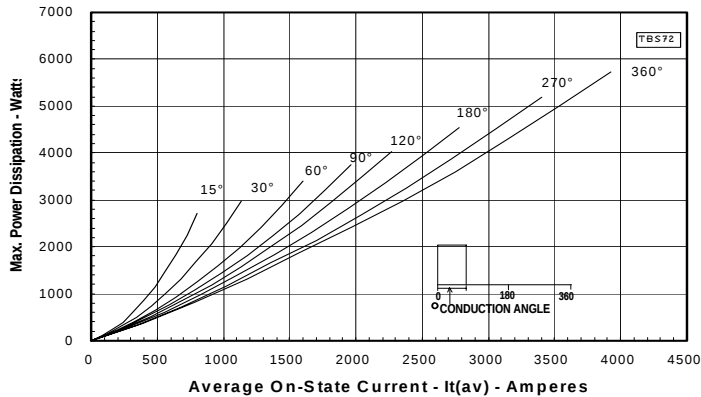
Maximum On-State Power Dissipation
(Sinusoidal)



Maximum Allowable Case Temperature
(Sinusoidal Waveform)



Maximum On-State Power Dissipation
(Rectangular Waveform)



Maximum Allowable Case Temperature
(Rectangular Waveform)

